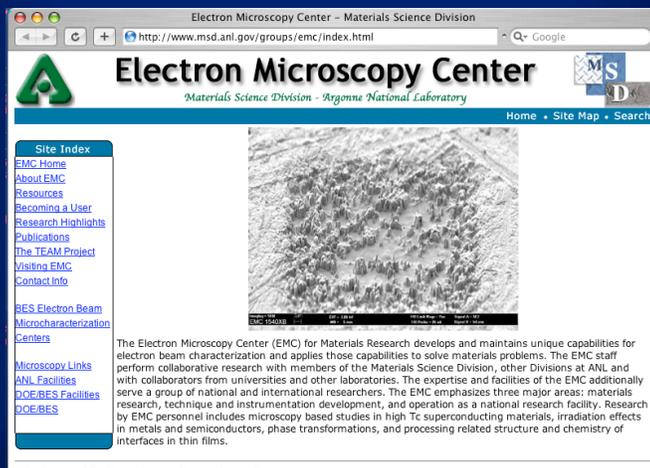


ANL Electron Microscopy Center
A DoE Basic Energy Science User Facility



<http://www.emc.anl.gov>

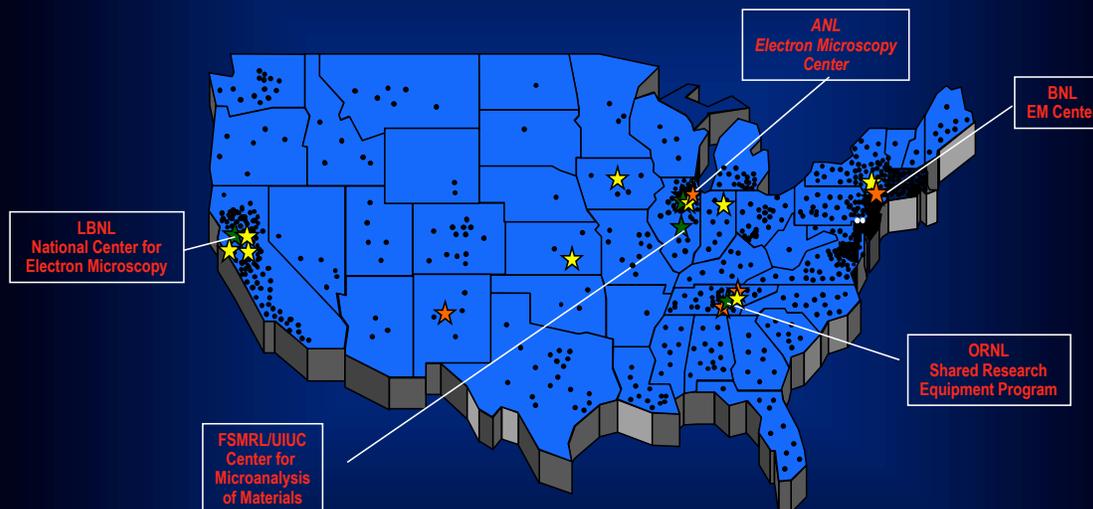


Office of Science - BES Program
 US Department of Energy

Electron Microscopy Center
 Materials Science, Division, Argonne National Laboratory



US DoE BES Program 18 Scientific User Facilities - 200 Institutions - > 1400 Research Projects



EMC Proposal Access Guidelines

One part of the EMC mission is to provide unique instrumentation and expertise to the scientific community. Important to achieving this goal is the effective management of EMC instrumentation and staff for maximum scientific impact. Broad and fair access to these resources is achieved through a proposal review process and scheduling and access policies.

The type of access granted is based on the nature of the proposed work, the qualifications of the user, and the instrumentation requested. Research projects may be allocated a specific amount of instrument time or may be granted continuous access.

Allocated Access:

Under *allocated access*, a user is allocated a specific amount of instrument time to complete the proposed project. Allocated access is utilized primarily to manage instrument time for those instruments that have very high demand and for projects that require exceptional staff assistance.

All new users and new projects will be designated for allocated access during the qualification and feasibility period.

Allocated access is utilized for research on the IVEM-Tandem, FEI Tecnai F20ST, LEO 1540XB, and all assisted user research.

Continuous Access:

Continuous access allows a user to use specified EMC instrumentation without limits on the amount of instrument time. Continuous access is intended for those users for whom Argonne is their primary research home or who otherwise demonstrate a consistent need for access to EMC instruments. Continuous access proposals terminate at the end of each fiscal year and must be renewed annually.

A user must attain at least *User* status for each instrument utilized under continuous access. Typically, the Hitachi S-4700-II, Philips CM30T, JEM-4000EXII, and JEM-100CXII are utilized under continuous access for *Users* and *Operators*.

Research projects may operate under both access policies. This may be the case when a research project requires the use of several instruments, for example.

Rapid Access:

Recognizing the occasional urgent need, a proposal may be granted rapid access at the discretion of the EMC Director. Rapid access is intended to facilitate discovery and dissemination of significant, new scientific results and may be granted if an exceptional case is presented. Rapid access is not intended to accommodate poor planning or other experimental difficulties.

The screenshot displays the website for the Electron Microscopy Center (EMC) at Argonne National Laboratory. The browser window title is "EMC - Resources" and the address bar shows "http://www.msd.anl.gov/groups/emc/resources/index.html". The page features a navigation menu on the left with links such as "Site Index", "EMC Home", "About EMC", "Resources", "Becoming a User", "Research Highlights", "Publications", "The TEAM Project", "Visiting EMC", "Contact Info", "BES Electron Beam Microcharacterization Centers", "Microscopy Links", "ANL Facilities", "DOE/BES Facilities", and "DOE/BES". The main content area is titled "Facilities and Resources" and contains the following text:

The instrumentation in the Center is organized according to specialized functions. Major areas in the Center include the IVEM-Tandem, the Analytical Electron Microscopy facility, the Advanced Analytical Electron Microscope, Specimen Preparation, and the Computing Center. In addition, a variety of other resources are available through collaboration with scientists in MSD. These resources are summarized below.

IVEM-Tandem

This unique facility consists of an intermediate voltage TEM (Hitachi H-9000 NAR) interfaced to two ion accelerators. This combination allows in situ observation of ion beam modification and effects of irradiation. In addition, a number of holders allow for a variety of in situ experiments to be performed, including low temperature studies in a liquid He stage. The accelerators also are used independently for ion beam irradiation/implantation and analysis including research for other programs. More information on the IVEM-Tandem is available at <http://www.msd.anl.gov/groups/ht/>.

AEM

The Analytical Electron Microscopy facility consists of electron microscopes that are optimized for high resolution and/or analytical work. This part of the Center primarily serves a regional and local user community.

Current instrumentation in the AEM includes:

- FEI Tecnai F20ST – analytical TEM and STEM
- JEM-4000EXII – high-resolution TEM
- Philips CM30T – analytical TEM
- JEM-100cx-II - TEM
- Hitachi S-4700-II – high resolution SEM
- LEO 1540XB – dual beam FIB

Additional information on the AEM facility is available at [here](#) [pdf - 121K].

AAEM and Materials Microcharacterization Collaboratory (MMC)

The Advanced Analytical Electron Microscope is a STEM/TEM with various modes, Telepresence, CTEM, CBED, EELS, windowless EDXS, CCD TV-rate imaging, SIMS, gas reaction cell, energy filtering, etc. This instrument serves primarily as a test-bed for the development of new techniques and methods. More information on the IVEM-Tandem is available at <http://www.amc.anl.gov>.

Specimen Preparation

Specimen preparation is an important part of electron microscopy. The EMC maintains an array of specimen preparation capabilities that are available to users. While users are expected to carry out their own specimen preparation, expertise and guidance may be provided by EMC or other MSD staff. The staff in the EMC have developed a number of new methods and approaches to sample preparation.

Image Analysis Laboratory

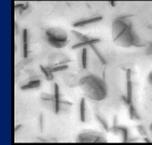
Open <http://www.msd.anl.gov/groups/ht/> in a new window behind the current window.

Microscopy & Microanalysis

Experimental methodologies which employ (electron-optical) instrumentation to spatially characterize matter on scales which range from tenths of a millimeter to tenths of a nanometer. The principle modalities employed are:

Imaging

- Transmission Electron Microscopy
- Scanning Transmission Electron Microscopy
- Scanning Electron Microscopy
- Focussed Ion Beam



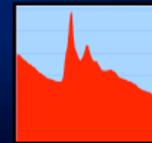
Diffraction

- Convergent Beam Electron Diffraction
- Selected Area Electron Diffraction
- Reflection High Energy Electron Diffraction



Spectroscopy

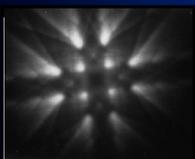
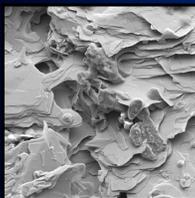
- X-ray Energy Dispersive
- Electron Energy Loss
- Auger Electron



MicroCharacterization via Electron Microscopy

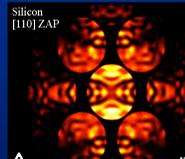
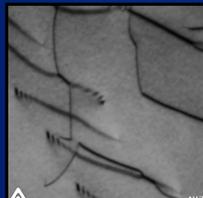
SEM

Scanning Electron Microscopy



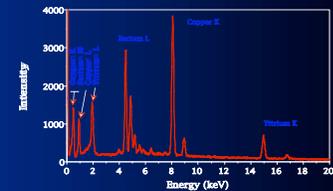
TEM - STEM - HREM

Transmission - Scanning Transmission - High Resolution Electron Microscopy



AEM

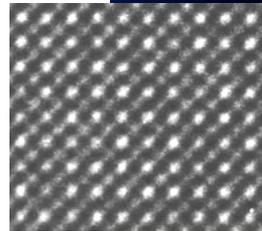
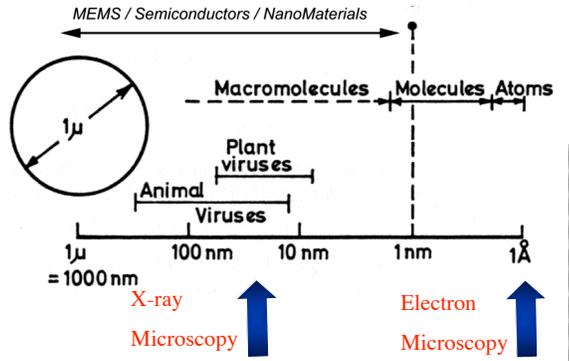
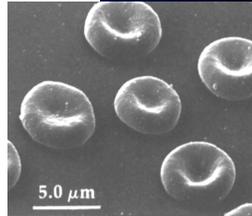
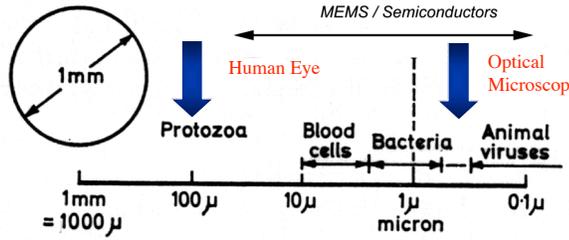
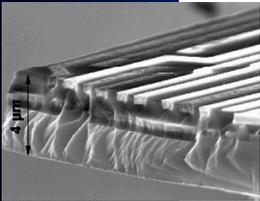
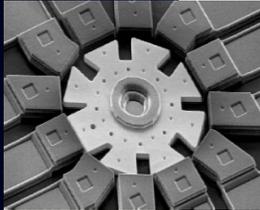
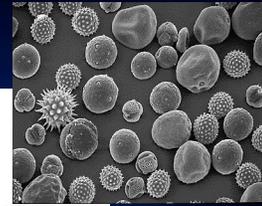
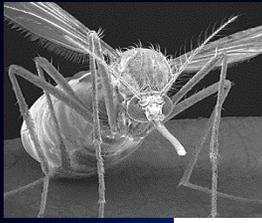
Analytical Electron Microscopy



Morphology, Crystallography, Elemental, Chemical, Electronic Structure

From Ants to Atoms

Microscopy is needed nearly everywhere



JEOL 4000



Philips CM30



Tecnai F20



Hitachi H-9000



Hitachi S4700



LEO 1540 XB SEM/FIB



Philips EM420

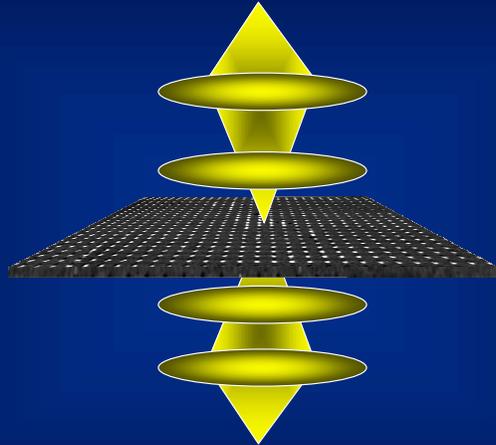


JEOL 100CX



AAEM VG HB603Z

Scanning Microscopy
Deals Mainly with Near Surface Region

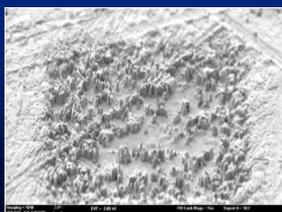
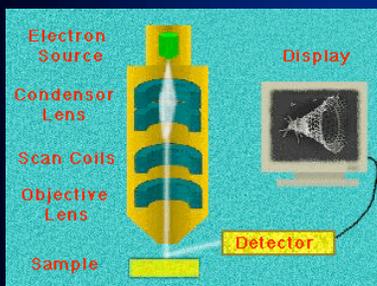
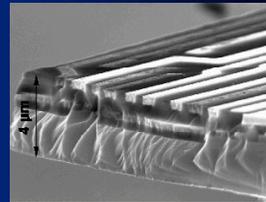
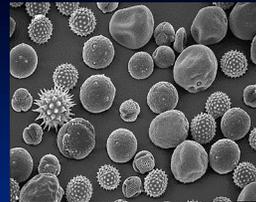


Transmission Microscopy
Deals Mainly with Internal Structure

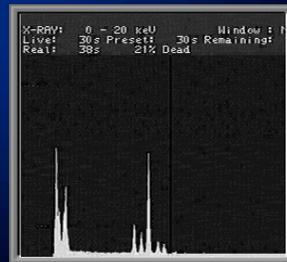
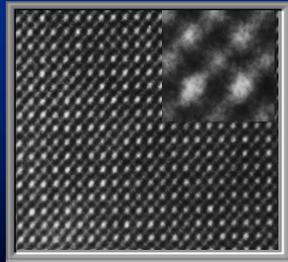
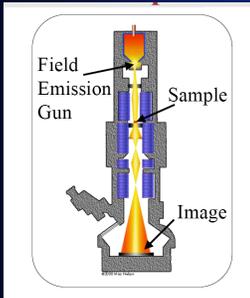
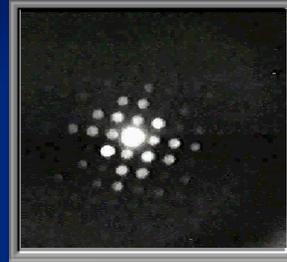
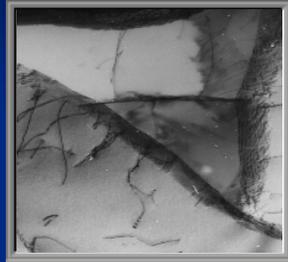
Scanning Electron
Microscopy



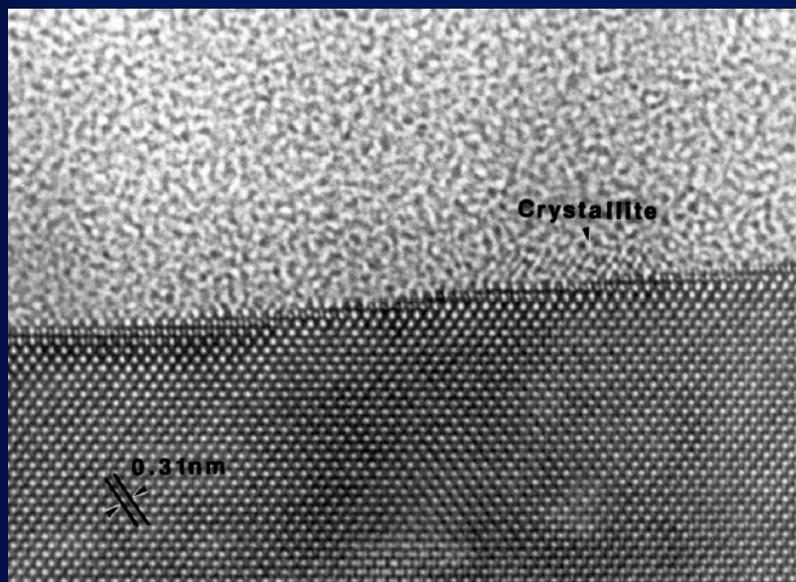
Hitachi S4700



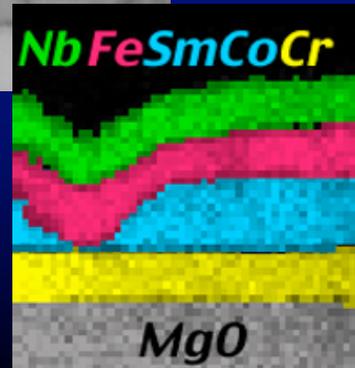
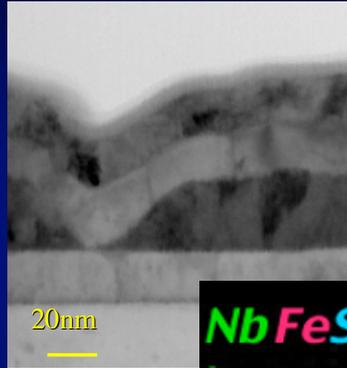
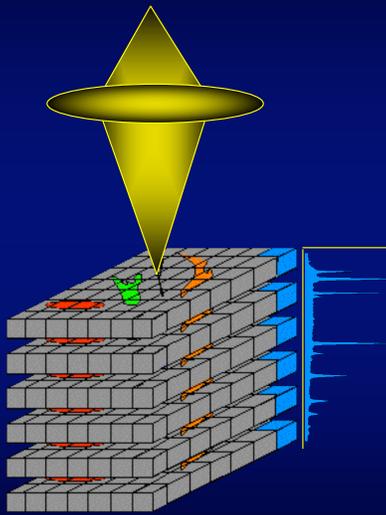
Transmission Electron Microscopy



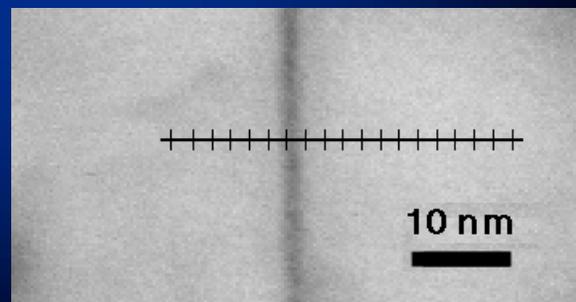
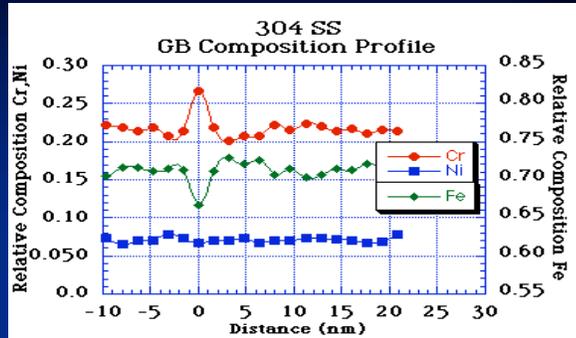
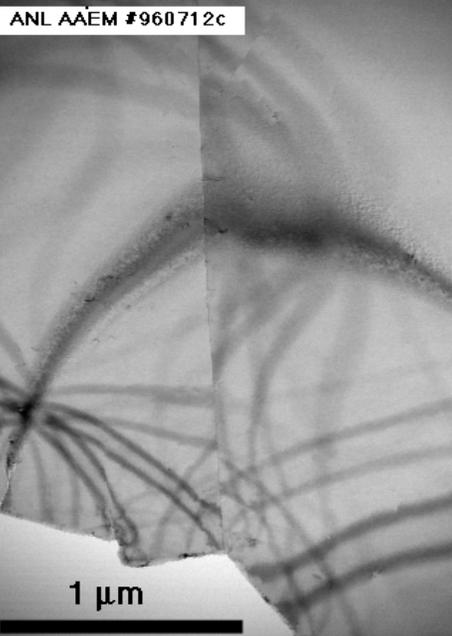
TEM-High Spatial Resolution Imaging



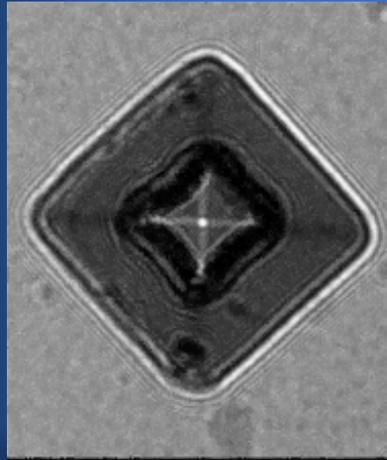
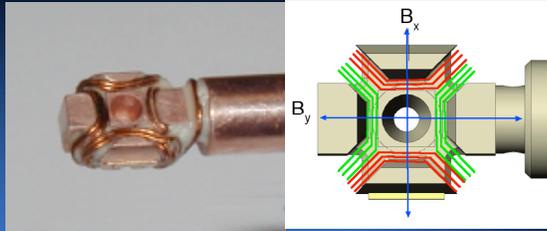
Spectral Imaging



AEM - High Spatial Resolution Measurements of GB Segregation in 304 /316 SS



In-Situ Stage for Dynamic Magnetization Studies



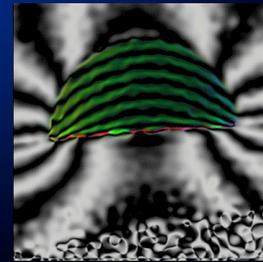
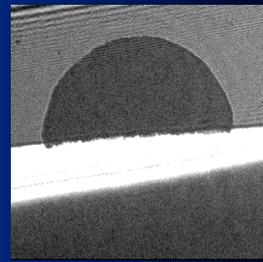
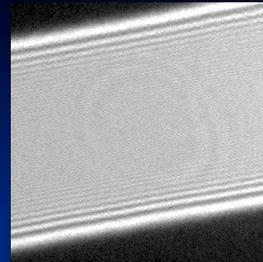
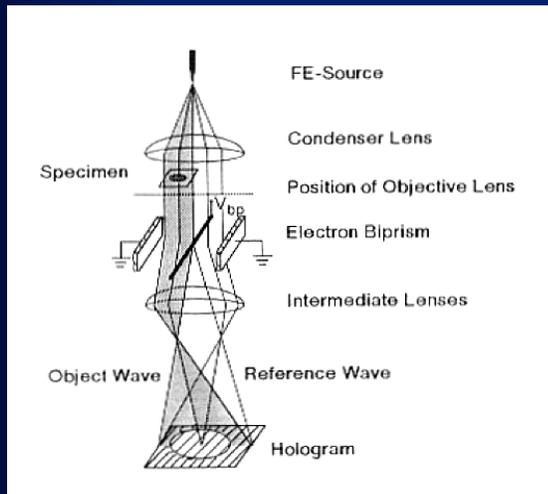
Magnetic Vortex Motion
in response to
Vertical & Horizontal
Applied Fields



Jan 2004
ANL Lorentz Stage Test
zaluzec@aaem.amc.anl.gov

000Title.psd

High Coherence Electron Holography



Feynman's Challenge

It would be very easy to make an analysis of any complicated chemical substance; all one would have to do would be to look at it and see where the atoms are. The only trouble is that the electron microscope is one hundred times too poor ... I put this out as a challenge: Is there no way to make the electron microscope more powerful?

– Richard P. Feynman, 1959

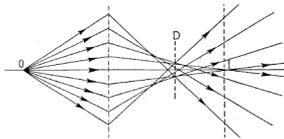
“There’s Plenty of Room at the Bottom”



What are the limitations:?

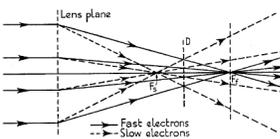
Aberrations

- Spherical

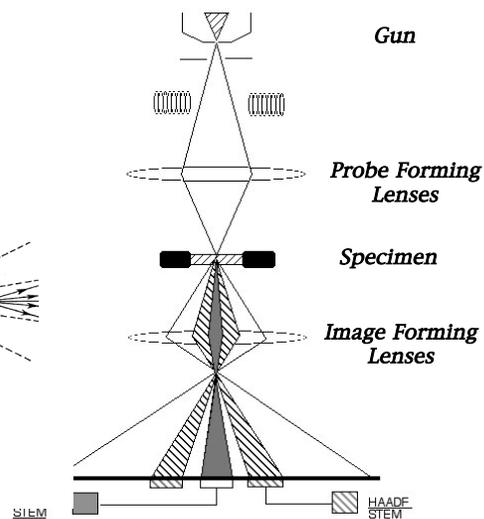


$$r_{sph} = C_s \beta^3$$

- Chromatic

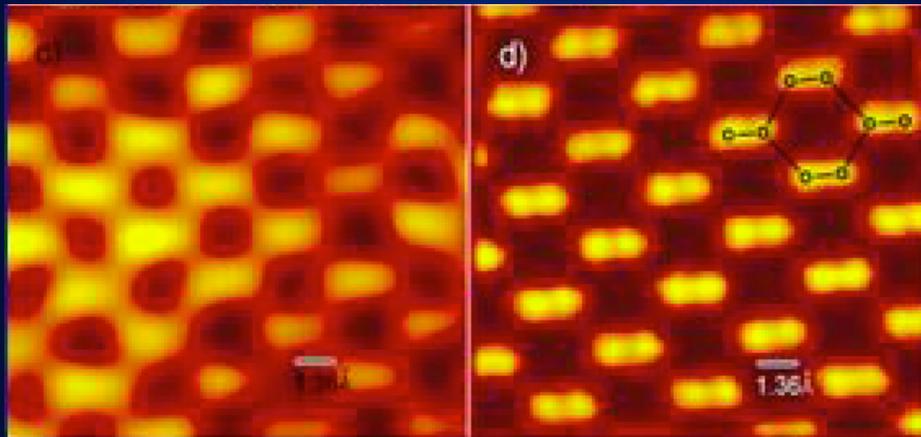


$$r_{chr} = C_c \frac{\Delta E}{E} \beta$$



What is the Limit of Current Technology In Aberration Correction

Silicon (110)



Before Correction

After Correction

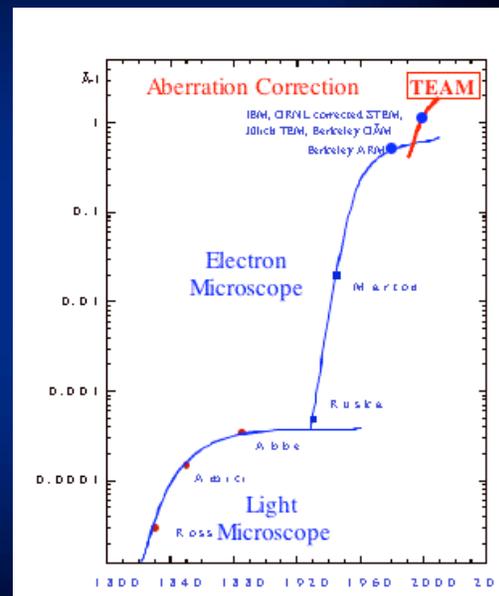
P.E. Batson IBM Yorktown, Jan 2004



Office of Science - BES Program
US Department of Energy

TEAM Project

- A Series of Breakthroughs in electron optics has minimized the barrier that is limiting the performance of electron microscopes
- Simultaneous advances in electronics, detectors, MEMS and computers enables the technology to be practically implemented
- Nanoscience and Nanotechnology Centers need atomic level characterization
- DOE recognizes the importance and is investing in the development



H. Rose, 2000

Transmission Electron Aberration-corrected Microscope (TEAM)



• **Goals:** To capitalize on recent advances in electron optics to design, build and operate the next generation of electron microscopes capable of 0.5 Å resolution in real time and with 3D with single atom sensitivity

• **Resign** the basic electron microscope around aberration corrected optics to serve as a platform for a suite of new instruments with unparalleled performance



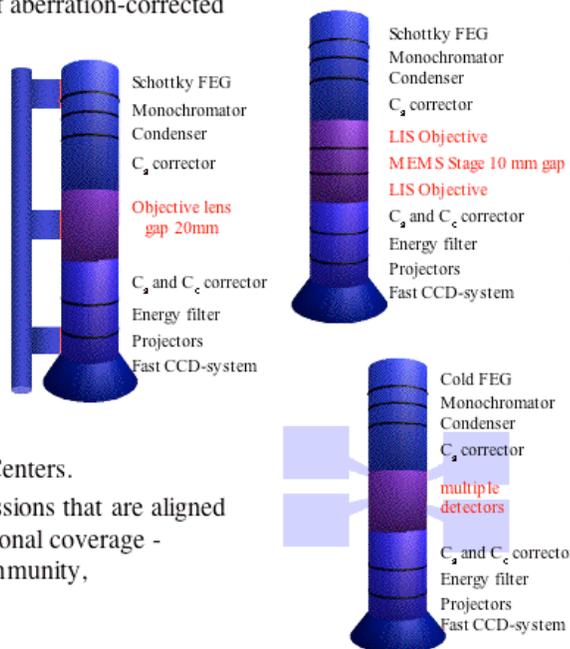
US DoE BES Program 18 Scientific User Facilities - 200 Institutions - > 1400 Research Projects



Based on TEAM platform, develop suite of aberration-corrected instruments for

- In-situ synthesis
- UHV environment
- Ultimate microanalysis
- Fast dynamics
- Lorentz imaging, ...

- Stimulate revitalization of electron optics in US.
- Instruments to be remotely accessible as a “distributed facility”.
- Proximity to nation’s synchrotron light and neutron sources and Nanoscience Centers.
- Well established user programs with missions that are aligned with BES science goals and provide national coverage - geography, scientific expertise, user community, instrumentation.

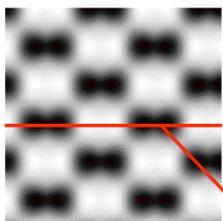




Goals: High-Resolution TEM & STEM

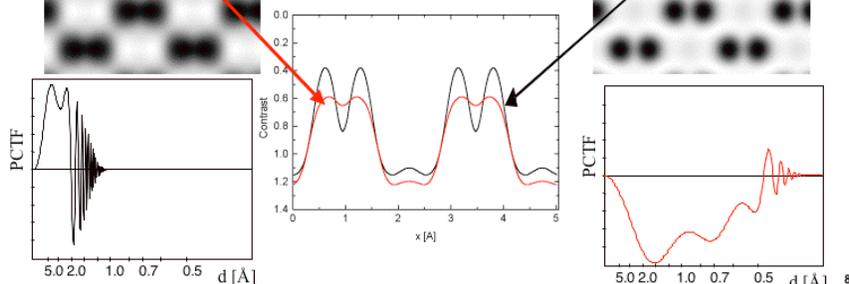
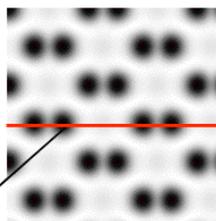
One order of magnitude gain in contrast

uncorrected: OAM



Diamond (110)

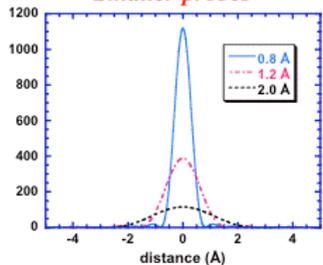
corrected: TEAM



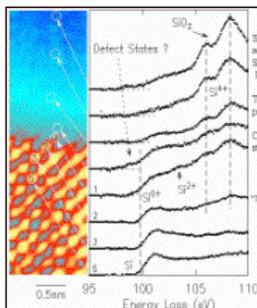
B. Kabius - ANL



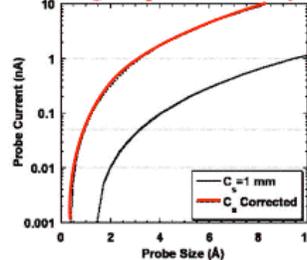
Smaller probes



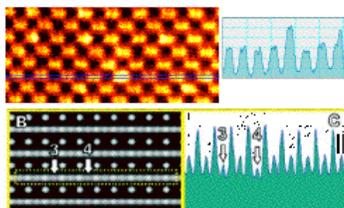
More signal



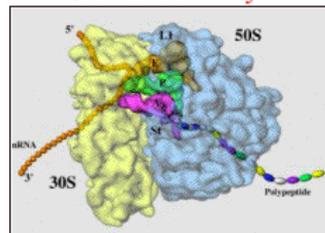
Higher probe intensity



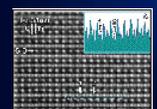
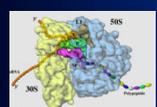
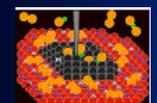
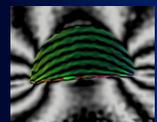
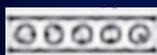
Greater contrast



Greater sensitivity



Benefits of Aberration Correction



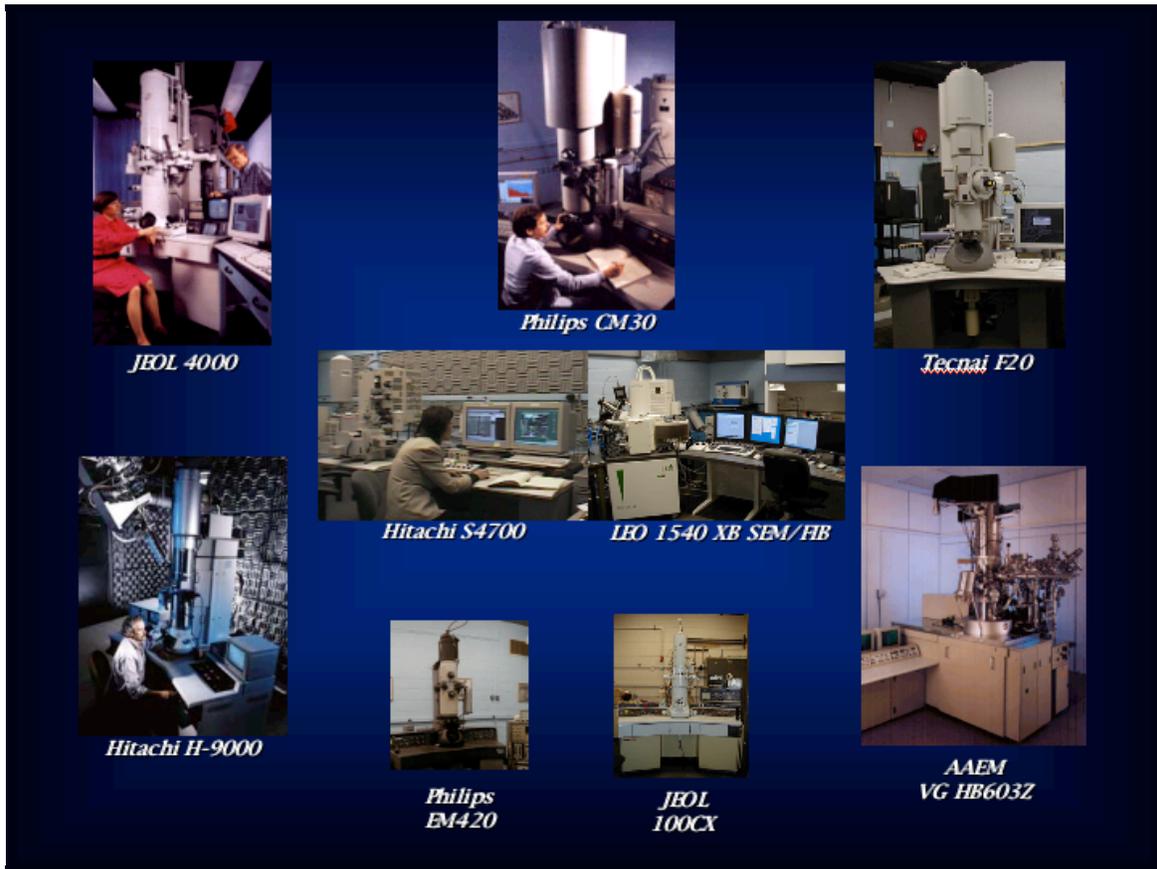
- Nanomaterials: Synthesis, properties, assembly, electronic structure
- Semiconductors: End of the Road Map in Si Tech.
- Magnetic Materials: fundamental understanding of magnetic nanostructures
- Photonic Materials: Effects of dopants, point defects
- Catalysis: Energy, environment, transportation: controlled chemical process
- Hard/Soft Materials: Increased sensitivity and resolution
- Oxidation/Corrosion: Real Time In-situ Experiments
- Superconductivity: Imaging and Spectroscopy at the highest levels.



Extraordinary Scientific Opportunities using direct observation of individual nanostructures

- *three dimensional atomic-scale structure, shape and defect distribution*
- *spectroscopic characterization and location of individual dopant atoms*
- *direct imaging of atomic scale structure of glasses*
- *electronic structure of individual point defects*
- *non-spherical charge density and valence electron distributions*
- *in-situ synthesis of novel nanoscale structures*
e.g. electron beam lithography with sub-Angstrom beams
- *in-situ observation of properties and response of materials to external variables*
temperature
stress/strain
environment & chemical activity
applied electric & magnetic fields

..... All with unprecedented spatial, spectral and temporal resolution



Characteristics and Capabilities of Argonne's Electron Microscopes

Instrument	Operating Modes	Specimen Holders	Resolution
JEOL JEM-100CXII 10 – 100 kV	CTEM, Lorentz (LMI) at high-magnifications*, SEM, STEM.	<i>Double Tilt</i> ($\pm 60^\circ \alpha, \pm 36^\circ \beta$): double specimen, Be cup for EDXS, & cooling (93 K) with Be cup. <i>Single Tilt</i> : double specimen & bulk.	~0.7 nm point ~0.3 nm line (standard)
Philips CM30T $\leq 50 - 300$ kV	CTEM, CBED, hollow-cone DF, light element EDXS, PEELS, electron dosimetry.	<i>Double Tilt</i> ($\pm 60^\circ \alpha, \pm 30^\circ \beta$): Be cup for EDXS, cooling (93 K) with Be cup, & heating (1250 K). <i>Single Tilt</i> : one. <i>Tilt/rotate</i> ($\pm 60^\circ, 360^\circ$): one.	~0.25 nm point ~0.14 nm line probe size ≥ 9 nm
JEOL JEM-4000EXII 100 – 400 kV VG HB603Z* 50 – 300 kV (cold FEG)	HREM, CTEM, TV-rate video, digital imaging via slow scan-rate CCD camera, electron dosimetry. STEM/TEM with various modes, Telepresence, CTEM, CBED, EELS, windowless EDXS, CCD TV-rate imaging, SIMS, gas reaction cell, energy filtering, etc.	<i>Top-Entry Double Tilt</i> ($\pm 20^\circ$): three. <i>Top-Entry Zero Tilt</i> : two.	~0.165 nm point ~0.1 nm line Lattice: ~0.2 nm (STEM) ~0.4 nm (CTEM) Probe size < 1 nm
Hitachi H-9000NAR* 100 – 300 kV	CTEM, <i>in situ</i> irradiation, ion dosimetry, TV-rate high resolution video, light element EDXS.	<i>Double Tilt</i> ($\pm 30^\circ$): heating (1250 K) & cooling (15 K – RT). <i>Single Tilt</i> : straining, electrical bias, & ion/electron dosimetry.	~0.25 nm pt-pt ~0.14 nm lattice
Hitachi S-4700-II SEM 0.5 – 30 kV (cold FEG)	SEI & BEI, light element EDXS with quantitative mapping.	5-axis motorized stage. Maximum sample size: 27 mm (H) x 150 mm (dia.).	SEI resolution: 1.5 nm at 15 kV 2.5 nm at 1.0 kV
FEI Tecnai F20ST 80 – 200 kV (Schottky FEG)	CTEM, STEM (BF/ADF, HAADF), CBED, light element EDXS, PEELS, Energy-filtered imaging (EFI), Lorentz magnetic imaging (LMI), electron holographic imaging (EHI), TV-rate video, etc.	<i>Double Tilt</i> ($\pm 40^\circ \alpha, \pm 30^\circ \beta$): Be cup for EDXS. <i>Single Tilt</i> ($\pm 40^\circ$): one. Compustage. Other Philips holders.	~0.24 nm point ~0.1 nm line Cs obj. ≈ 1.2 nm Cc obj. ≈ 1.2 nm probe $\approx 0.2-1$ nm